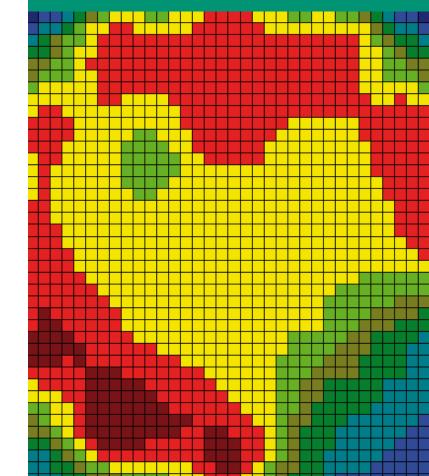






FRAUNHOFER INSTITUTE FOR INTEGRATED SYSTEMS AND DEVICE TECHNOLOGY IISB

VACUUM ULTRA-VIOLET REFLECTOMETRY (VUV-R)



VUV-R APPLICATIONS

- High-k dielectric materials
- Ultra-thin layer < 10 nm
- Layer thickness mapping
- Material concentration
- Optoelectronics
- Photovoltaic

CONTACT

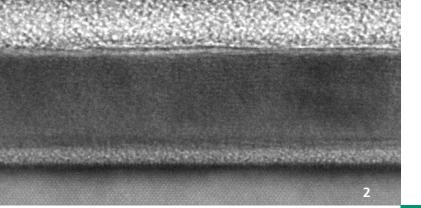
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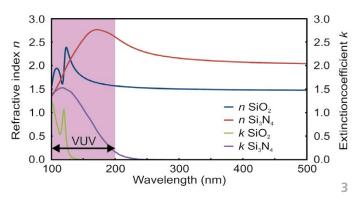
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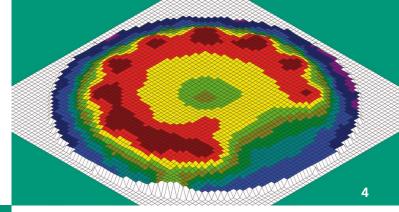
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VUV-R PROPERTIES & BENEFITS

Ultra-thin film measurement

- Non-destructive dielectric film characterization for new applications in semiconductor manufacturing
- Film composition and material concentration
- Multi-layer characterization

Fully automated measurement

- Spectral region 120 nm 800 nm
- 200 mm 300 mm wafer
- Small spot size 35 µm x 35 µm
- Unpatterned and patterned

High throughput

Fast wafer mapping

Materials

 E.g. SiO₂, Si₃N₄, Al₂O₃, Hf-based oxides, ONO, TiO₂, ZrO₂

PRINCIPLE OF VUV-R*

Key semiconductor materials have unique absorption peaks at short VUV wavelengths < 200 nm

- Characterization of ultra thin layers by saturation of the absorption properties at DUV and VUV by acquisition of the band gap
- Layer separation due to different material properties
- Measurement of difference in the intensities between the light reflected from the sample and the incidence light source

OUR OFFERS

R&D activities

- Characterization of new high-k dielectric materials
- Calculation of optical properties
- Measurement of film thickness and material concentration
- Detection of surface contamination

Standard measurements

- Layer thickness
- Material concentration
- Wafer mapping

^{*} VUV: Vacuum Ultra Violet Wavelengths, 100 nm - 800 nm